

A N Anagnostopoulos

List of Publications by Year in descending order

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32
papers

525
citations

623734

14
h-index

677142

22
g-index

34
all docs

34
docs citations

34
times ranked

367
citing authors

#	ARTICLE	IF	CITATIONS
1	I-Udependence of TlInX ₂ (X=Se,Te) single crystals: The Ohmic and S-type regions. Physical Review B, 1991, 43, 4135-4140.	3.2	65
2	Negative-differential-resistance effects in the TlGaTe ₂ ternary semiconductor. Physical Review B, 1993, 47, 4261-4267.	3.2	55
3	Excitonic and other interband transitions in TlInS ₂ single crystals. Physical Review B, 1994, 50, 7488-7494.	3.2	50
4	Composition Faults in ZnIn ₂ S ₄ (III) Layered Crystals and Their Influence on the Anisotropic Conductivity of This Compound. Physica Status Solidi A, 1982, 72, 731-736.	1.7	31
5	Quasiperiodic and chaotic self-excited voltage oscillations in TlInTe ₂ . Physical Review B, 1994, 49, 16994-16998.	3.2	31
6	Optical investigation of SnS ₂ single crystals. Journal of Materials Science, 1996, 31, 5975-5978.	3.7	29
7	THE INTERMITTENCY ROUTE TO CHAOS OF AN ELECTRONIC DIGITAL OSCILLATOR. International Journal of Bifurcation and Chaos in Applied Sciences and Engineering, 2008, 18, 1561-1566.	1.7	26
8	Growth and characterization of SnSe ₂ . Journal of Materials Science, 1996, 31, 3647-3649.	3.7	19
9	Comparison of the Structure and the Electric Properties of ZnIn ₂ S ₄ (III)- and CdInGaS ₄ -Layered Crystals. Physica Status Solidi A, 1983, 77, 595-601.	1.7	18
10	Electrical conductivity of layered GeSe related to extended faults. Journal of Applied Physics, 1985, 58, 3917-3920.	2.5	18
11	Nonlinear electrical conductivity of V ₂ O ₅ single crystals. Physical Review B, 1992, 45, 11627-11631.	3.2	17
12	Conduction anisotropy in layered semiconductors. Physical Review B, 1994, 50, 14643-14646.	3.2	17
13	Large single-crystal growth and characterization of the narrow-gap semiconductor. Semiconductor Science and Technology, 1996, 11, 1405-1410.	2.0	16
14	Digital Chaotic Synchronized Communication System. Journal of Engineering Science and Technology Review, 2009, 2, 82-86.	0.4	15
15	Electrical effects associated with the ordering process in CdInGaS ₄ crystals. I. Electron microscopy and electron diffraction study. Physica Status Solidi A, 1983, 80, 503-511.	1.7	11
16	Influence of Composition Faults on the Anisotropic Conductivity of Layered Semiconductors. Physica Status Solidi A, 1982, 73, 91-94.	1.7	10
17	Influence of composition faults on the AC conductivity of ZnIn ₂ S ₄ (III). Physica Status Solidi A, 1983, 75, 595-599.	1.7	10
18	Temperature dependence of the energy gap and some electrical properties of Zn ₂ In ₂ S ₅ (II) single crystals. Semiconductor Science and Technology, 1989, 4, 536-542.	2.0	10

#	ARTICLE	IF	CITATIONS
19	Analysis of microhardness data in $\text{TeIn}_{1-x}\text{Se}$. Journal of Materials Science, 1995, 30, 5576-5580.	3.7	10
20	Electron trap distribution determined by means of conductivity measurements on highly anisotropic ZnIn_2S_4 crystals. Physica Status Solidi A, 1982, 71, 543-548.	1.7	9
21	Single crystal growth and characterization of narrow-gap - mixed crystals. Semiconductor Science and Technology, 1998, 13, 86-92.	2.0	9
22	Electrical behavior of extended twins present in layered GeSe. Journal of Applied Physics, 1986, 59, 2859-2862.	2.5	8
23	Chaotic voltage oscillations in the negative-differential-resistance region of the In_2O_5 crystals. Physical Review B, 1992, 46, 16144-16147.	3.2	7
24	Voltage-Dependent Conductivity along the c-Axis of ZnIn_2S_4 (III). Physica Status Solidi A, 1983, 79, 513-516.	1.7	5
25	Electronic behavior of Ga_2S_3 single crystals. Physical Review B, 1988, 37, 4026-4031.	3.2	4
26	Current pulses and high-frequency oscillations in a-Si/Si(p)/Si(n) heterojunction device. Semiconductor Science and Technology, 1999, 14, 897-900.	2.0	4
27	Dielectric behavior of mixed $\text{HgBr}_{1-x}\text{I}_x$ single crystals. Journal of Materials Science Letters, 2000, 19, 1019-1020.	0.5	4
28	Electrical properties of an a-Si/Si(p)/Si(n) heterojunction device. Semiconductor Science and Technology, 2000, 15, 980-984.	2.0	4
29	A Digital Nonautonomous Chaotic Oscillator Suitable for Information Transmission. IEEE Transactions on Circuits and Systems II: Express Briefs, 2013, 60, 887-891.	3.0	3
30	Electrical effects associated with the ordering process in CdInGaS_4 crystals. II. Electron traps determined with conductivity measurements. Physica Status Solidi A, 1985, 92, 231-235.	1.7	2
31	DIFFUSIONAL MODEL FOR NOISY ON-OFF INTERMITTENCY. International Journal of Bifurcation and Chaos in Applied Sciences and Engineering, 1999, 09, 355-359.	1.7	2
32	IN-OUT INTERMITTENT LOSS OF SYNCHRONIZATION IN TWO UNIDIRECTIONALLY COUPLED NONLINEAR FOURTH-ORDER AUTONOMOUS CIRCUITS. International Journal of Bifurcation and Chaos in Applied Sciences and Engineering, 2010, 20, 3329-3339.	1.7	1